

Si PIN photodiode

S4707-01

Si PIN photodiode for general photometry



Features

- Clear plastic package: 4.5 × 5.5 mm
- 4-pin DIP type
- Active area: 2.4 × 2.8 mm

Applications

- Optical switch, etc.

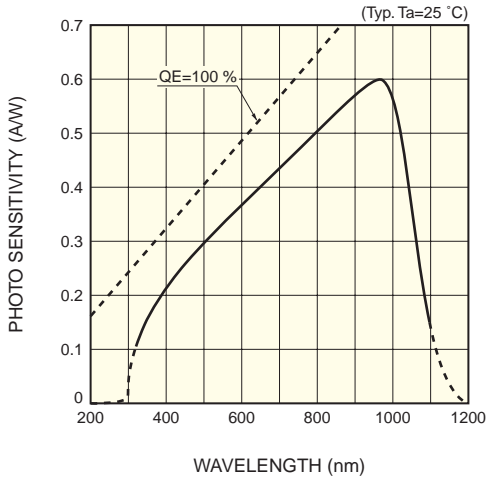
■ Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Value	Unit
Reverse voltage	VR Max.	20	V
Operating temperature	Topr	-25 to +85	°C
Storage temperature	Tstg	-40 to +100	°C

■ Electrical and optical characteristics (Ta=25 °C)

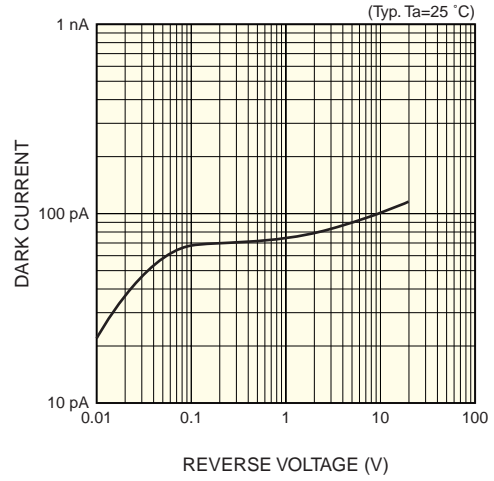
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Spectral response range	λ		-	320 to 1100	-	nm
Peak sensitivity wavelength	λ_p		-	960	-	nm
Photo sensitivity	S	$\lambda = \lambda_p$	0.5	0.6	-	A/W
Short circuit current	Isc	100 lx, 2856 K	-	6.6	-	μA
Dark current	ID	VR=10 V	-	0.08	5	nA
Cut-off frequency	fc	VR=10 V, RL=50 Ω -3 dB, $\lambda=780$ nm	-	20	-	MHz
Terminal capacitance	Ct	VR=10 V, f=1 MHz	-	14	30	pF

■ Spectral response



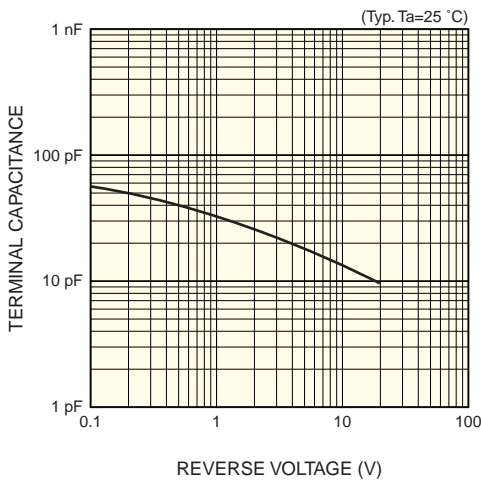
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■ Dark current vs. reverse voltage



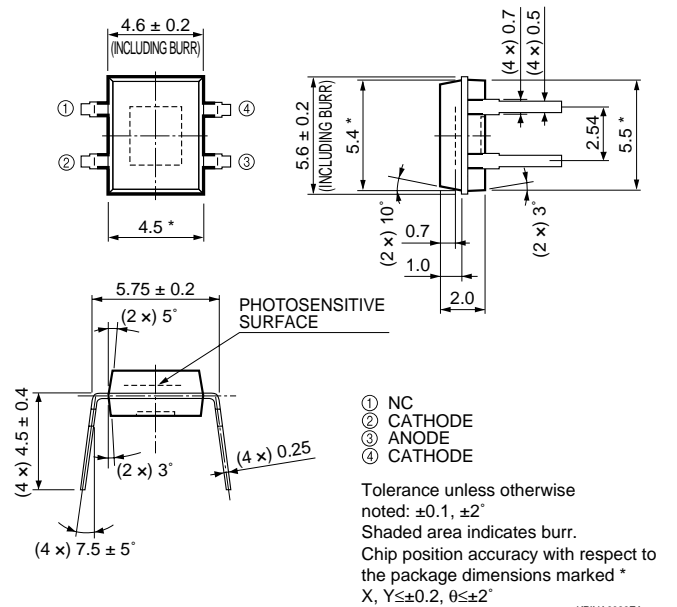
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■ Terminal capacitance vs. reverse voltage



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■ Dimensional outline (unit: mm)



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